FAIRCHILD SEMICONDUCTOR™

September 1983
Revised February 1999

MM74HC174
Hex D-Type Flip-Flops with Clear

General Description

The MM74HC174 edge triggered flip-flops utilize advanced silicon-gate CMOS technology to implement D-type flip-flops. They possess high noise immunity, low power, and speeds comparable to low power Schottky TTL circuits. This device contains 6 master-slave flip-flops with a common clock and common clear. Data on the D input having the specified setup and hold times is transferred to the Q output on the LOW-to-HIGH transition of the CLOCK input. The CLEAR input when LOW, sets all outputs to a low state.

Each output can drive 10 low power Schottky TTL equivalent loads. The MM74HC174 is functionally as well as pin compatible to the 74LS174. All inputs are protected from damage due to static discharge by diodes to V_{CC} and ground.

Features

- Typical propagation delay: 16 ns
- Wide operating voltage range: 2–6V
- Low input current: 1 μA maximum
- Low quiescent current: 80 μA (74HC Series)
- Output drive: 10 LSTTL loads

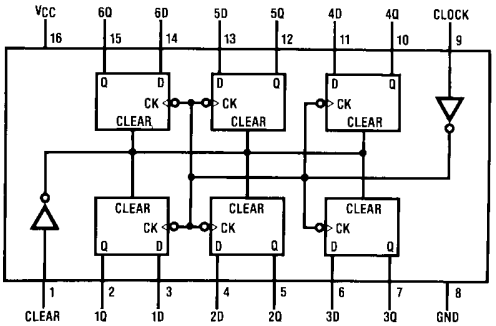
Ordering Code:

Order Number	Package Number	Package Description
MM74HC174M	M16A	16-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
MM74HC174SJ	M16D	16-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
MM74HC174MTC	MTC16	16-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
MM74HC174N	N16E	16-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide

Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.

Connection Diagram

Pin Assignments for DIP, SOIC, SOP and TSSOP



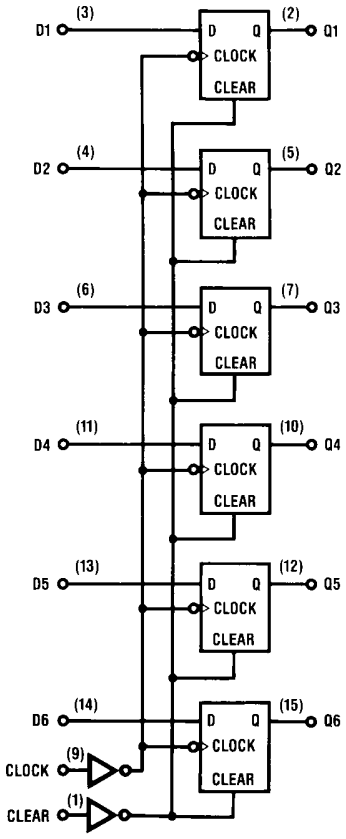
Truth Table

(Each Flip-Flop)

Inputs			Outputs
Clear	Clock	D	Q
L	X	X	L
H	↑	H	H
H	↑	L	L
H	L	X	Q_0

H = HIGH Level (steady state)
L = LOW Level (steady state)
X = Don't Care
↑ = Transition from LOW-to-HIGH level
Q_0 = The level of Q before the indicated steady state input conditions were established.

Logic Diagram



Absolute Maximum Ratings(Note 1)

(Note 2)

Supply Voltage (V_{CC})	−0.5 to +7.0V
DC Input Voltage (V_{IN})	−1.5 to V_{CC} +1.5V
DC Output Voltage (V_{OUT})	−0.5 to V_{CC} +0.5V
Clamp Diode Current (I_{IK}, I_{OK})	±20 mA
DC Output Current, per pin (I_{OUT})	±25 mA
DC V_{CC} or GND Current, per pin (I_{CC})	±50 mA
Storage Temperature Range (T_{STG})	−65°C to +150°C
Power Dissipation (P_D)	
(Note 3)	600 mW
S.O. Package only	500 mW
Lead Temperature (T_L)	
(Soldering 10 seconds)	260°C

Recommended Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage			
(V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temperature Range (T_A)	−40	+85	°C
Input Rise or Fall Times			
(t_r, t_f) V_{CC} = 2.0V		1000	ns
V_{CC} = 4.5V		500	ns
V_{CC} = 6.0V		400	ns

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: −12 mW/°C from 65°C to 85°C.

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V_{CC}	T_A = 25°C	T_A = −40 to 85°C	T_A = −55 to 125°C	Units
				Typ	Guaranteed Limits		
V_{IH}	Minimum HIGH Level		2.0V		1.5	1.5	1.5	V
	Input Voltage		4.5V		3.15	3.15	3.15	V
			6.0V		4.2	4.2	4.2	V
V_{IL}	Maximum LOW Level		2.0V		0.5	0.5	0.5	V
	Input Voltage		4.5V		1.35	1.35	1.35	V
			6.0V		1.8	1.8	1.8	V
V_{OH}	Minimum HIGH Level	V_{IN} = V_{IH} or V_{IL}						
	Output Voltage	$\|I_{OUT}\| \le 20\ \mu A$	2.0V	2.0	1.9	1.9	1.9	V
			4.5V	4.5	4.4	4.4	4.4	V
			6.0V	6.0	5.9	5.9	5.9	V
		V_{IN} = V_{IH} or V_{IL}						
		$\|I_{OUT}\| \le 4.0$ mA	4.5V	4.2	3.98	3.84	3.7	V
		$\|I_{OUT}\| \le 5.2$ mA	6.0V	5.7	5.48	5.34	5.2	V
V_{OL}	Maximum LOW Level	V_{IN} = V_{IH} or V_{IL}						
	Output Voltage	$\|I_{OUT}\| \le 20\ \mu A$	2.0V	0	0.1	0.1	0.1	V
			4.5V	0	0.1	0.1	0.1	V
			6.0V	0	0.1	0.1	0.1	V
		V_{IN} = V_{IH} or V_{IL}						
		$\|I_{OUT}\| \le 4.0$ mA	4.5V	0.2	0.26	0.33	0.4	V
		$\|I_{OUT}\| \le 5.2$ mA	6.0V	0.2	0.26	0.33	0.4	V
I_{IN}	Maximum Input Current	V_{IN} = V_{CC} or GND	6.0V		±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current	V_{IN} = V_{CC} or GND I_{OUT} = 0 μA	6.0V		8.0	80	160	μA

Note 4: For a power supply of 5V ±10% the worst case output voltages (V_{OH}, and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC} = 5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

AC Electrical Characteristics

V_{CC} = 5V, T_A = 25°C, C_L = 15pF, t_r = t_f = 6 ns

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
f_{MAX}	Maximum Operating Frequency		50	30	MHz
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Clock or Clear to Output		16	30	ns
t_{REM}	Minimum Removal Time, Clear to Clock		−2	5	ns
t_S	Minimum Setup Time Data to Clock		10	20	ns
t_H	Minimum Hold Time Clock to Data		0	5	ns
t_W	Minimum Pulse Width Clock or Clear		10	16	ns

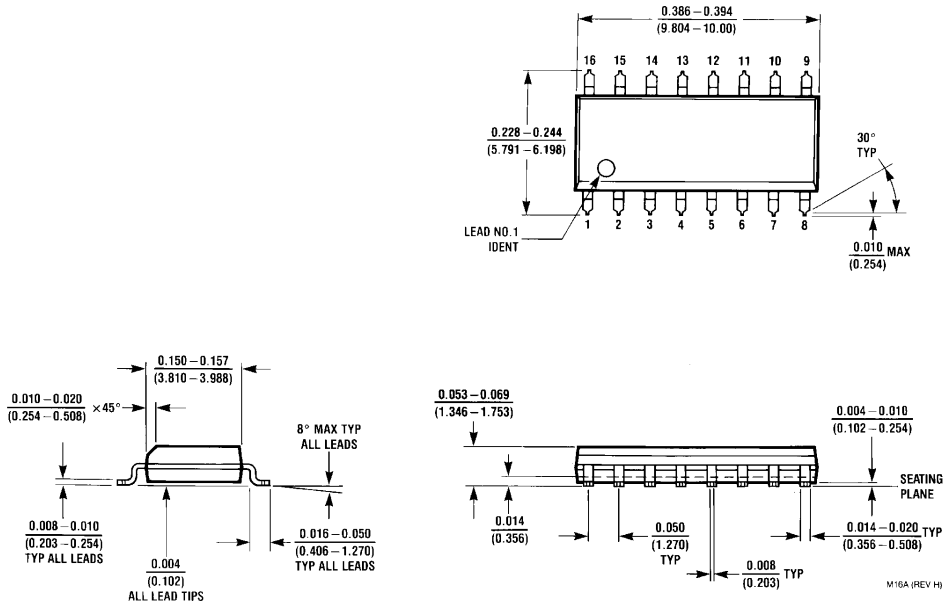
AC Electrical Characteristics

C_L = 50 pF, t_r = t_f = 6 ns (unless otherwise specified)

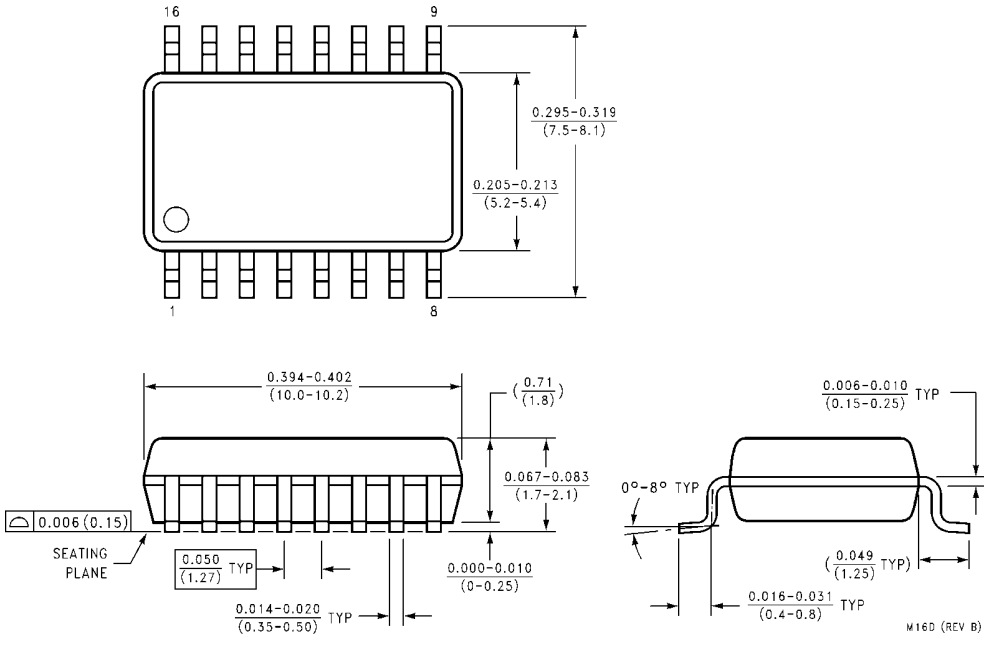
Symbol	Parameter	Conditions	V_{CC}	T_A = 25°C	T_A = −40 to 85°C	T_A = −55 to 125°C	Units
				Typ	Guaranteed Limits		
f_{MAX}	Maximum Operating Frequency		2.0V		5	4	3	MHz
			4.5V		27	21	18	MHz
			6.0V		31	24	20	MHz
t_{PHL}, t_{PLH}	Maximum Propagation Delay Clock or Clear to Output		2.0V	55	165	206	248	ns
			4.5V	18	33	41	49	ns
			6.0V	16	28	35	42	ns
t_{REM}	Minimum Removal Time Clear to Clock		2.0V	1	5	5	5	ns
			4.5V	1	5	5	5	ns
			6.0V	1	5	5	5	ns
t_S	Minimum Setup Time Data to Clock		2.0V	42	100	125	150	ns
			4.5V	12	20	25	30	ns
			6.0V	10	17	21	25	ns
t_H	Minimum Hold Time Clock to Data		2.0V	1	5	5	5	ns
			4.5V	1	5	5	5	ns
			6.0V	1	5	5	5	ns
t_W	Minimum Pulse Width Clock or Clear		2.0V	35	80	106	120	ns
			4.5V	10	16	20	24	ns
			6.0V	8	14	18	20	ns
t_{TLH}, t_{THL}	Maximum Output Rise and Fall Time		2.0V	30	75	95	110	ns
			4.5V	8	15	19	22	ns
			6.0V	7	13	16	19	ns
t_r, t_f	Maximum Input Rise and Fall Time		2.0V		1000	1000	1000	ns
			4.5V		500	500	500	ns
			6.0V		400	400	400	ns
C_{PD}	Power Dissipation Capacitance (Note 5)	(per package)		136				pF
C_{IN}	Maximum Input Capacitance			5	10	10	10	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

Physical Dimensions inches (millimeters) unless otherwise noted

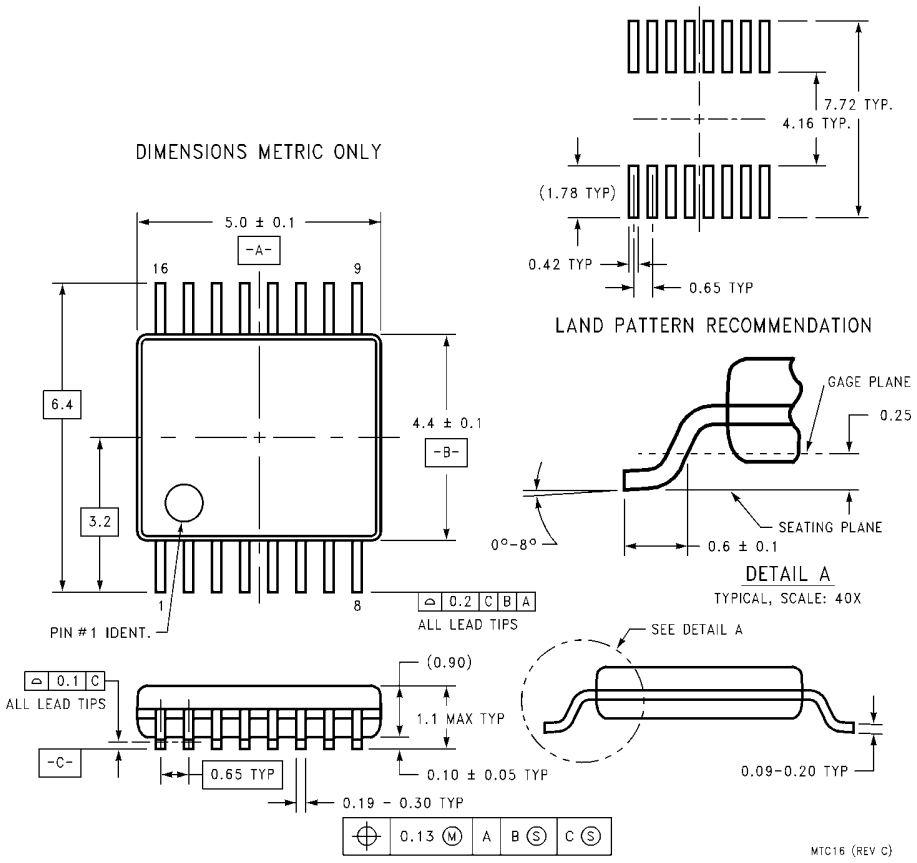


16-Lead Small Outline Integrated Circuit (SOIC)JEDEC MS-012, 0.150" Narrow
Package Number M16A



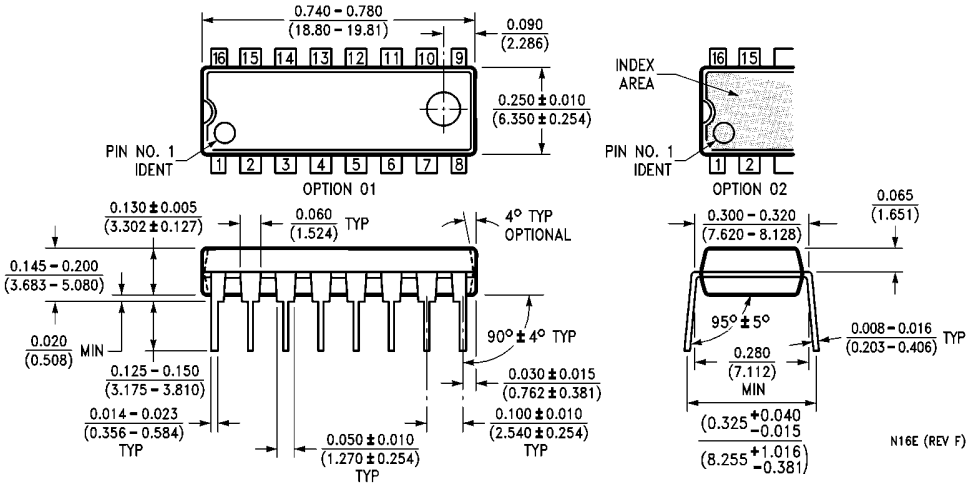
16-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
Package Number M16D

Physical Dimensions inches (millimeters) unless otherwise noted (Continued)



16-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
Package Number MTC16

Physical Dimensions inches (millimeters) unless otherwise noted (Continued)



16-Lead Plastic Dual-In Line Package (PDIP), JEDEC MS-001, 0.300" Wide
Package Number N16E